

PULSED LASER DIODES

850 nm **NEW**

part number	Preliminary specifications (@ 21°C, 150 ns, 6.66kHz)					
	wavelength nm	typ. power Watt	package	emitting area μm x μm	lop A	lth mA
850D1S03X	850	5	U,S	75 x 1	7	300
850D1S06X	850	11	U,S	150 x 1	15	600
850D1S09X	850	17	U,S	230 x 1	22	900
850D1S12X	850	23	U,S	300 x 1	30	1200
850D1S16X	850	30	U,S	400 x 1	40	1500
850D2S06X	850	22	U,S	150 x 125	15	600
850D3S09X	850	45	U,S	230 x 225	22	900
850D3S12X	850	60	U,S	300 x 225	30	1200
850D4S12X	850	80	U,S	300 x 340	30	1200
850D4S16X	850	100	U,S	400 x 340	40	1500

Option: C, R, Y package

1550 nm

part number	specifications (@ 21°C, 150 ns, duty factor= 0.1%)					
	wavelength nm	min power Watt	package	emitting area μm x μm	lop A	lth mA
155G1S06X	1550	5	S	150 x 1	20	1
155G1S14X	1550	12	S	350 x 1	40	1.5
155G2S06X	1550	10	S	150 x 150	20	1
155G4S14X	1550	45	S	350 x 340	40	1.5

Option: R package



Preliminary generic characteristics at 21°C				
	min	typ	max	units
wavelength	840	850	860	nm
spectral bandwidth		5		nm
temperature coefficient		0.27		nm/°C
beam spread				
parallel to junction plane		12		degrees
perpendicular				
single element		30		degrees
stacks		35		degrees
reverse voltage		6		V
pulse duration				
single element			1	μs
stacks			200	ns
duty factor			0.1	%
temperature				
storage	-55		100	°C
operating	-45		85	°C

generic characteristics at 21°C				
	min	typ	max	units
wavelength	1520	1550	1580	nm
spectral bandwidth		12		nm
temperature coefficient		0.6		nm/°C
beam spread				
parallel to junction plane		10		degrees
perpendicular				
single element		48		degrees
stacks		48		degrees
reverse voltage			2	V
pulse duration				
single element			200	ns
stacks			150	ns
duty factor			0.1	%
temperature				
storage	-55		100	°C
operating	-45		85	°C



PULSED LASER DIODES

905 nm

part number	specifications (@ 21°C, 150 ns, 6.66kHz)					
	wavelength nm	min power Watt	package	emitting area μm x μm	lop A	lth mA
905D1S1.5X	905	3	U,S	37.5 x 1	3,5	100
905D1S03X	905	6	U,S	75 x 1	7	200
905D1S06X	905	13	U,S	150 x 1	15	400
905D1S09X	905	19	U,S	230 x 1	22	600
905D1S12X	905	26	U,S	300 x 1	30	800
905D1S16X	905	34	U,S	400 x 1	40	1200
905D2S06X	905	25	U,S	150 x 125	15	400
905D3S09X	905	55	U,S	230 x 225	22	600
905D3S12X	905	70	U,S	300 x 225	30	800
905D4S12X	905	90	U,S	300 x 340	30	800
905D4S16X	905	130	U,S	400 x 340	40	1200

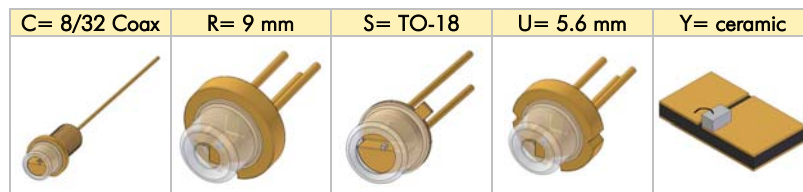
Option: C, R, Y package

905 nm Multi-junction devices **NEW**

part number	Preliminary specifications (@ 21°C, 100 ns, 6,66 kHz)					
	wavelength nm	min power Watt	package	emitting area μm x μm	lop A	lth mA
905D1S2J03X	905	15	U,S	80 x 5	8	310
905D1S2J09X	905	40	U,S	230 x 5	22	1050
905D1S3J08X*	905	70	U,S	200 x 10	40	750
905D2S3J08X*	905	140	U,S	200 x 125	40	750
905D3S3J08X*	905	210	U,S	200 x 250	40	750

Option: C, R, Y package

*(specifications @ 21°C, 100 ns, 1 kHz)



generic characteristics at 21°C				
	min	typ	max	units
wavelength	895	905	915	nm
spectral bandwidth		5		nm
temperature coefficient		0.27		nm/°C
beam spread				
parallel to junction plane		12		degrees
perpendicular				
single element		25		degrees
stacks		30		degrees
reverse voltage			6	V
pulse duration				
single element			1	μs
stacks			200	ns
duty factor			0,1	%
temperature				
storage	-55		100	°C
operating	-45		85	°C

generic characteristics at 21°C				
	min	typ	max	units
wavelength	895	905	915	nm
spectral bandwidth		8		nm
temperature coefficient		0.28		nm/°C
beam spread				
parallel (2J devices)		15		degrees
perpendicular (2J devices)		20		degrees
parallel (3J devices)		11		degrees
perpendicular (3J devices)		25		degrees
reverse voltage (2J devices)		6		V
reverse voltage (3J devices)		3		V
pulse duration				
single element			100	ns
stacks			100	ns
duty factor			0.1	%
temperature				
storage	-55		100	°C
operating	-45		85	°C

